

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC5087

VHF~UHF Band Low Noise Amplifier Applications

Unit: mm

- Low noise figure, high gain.
- $NF = 1.1\text{dB}$, $|S_{21e}|^2 = 13\text{dB}$ ($f = 1\text{ GHz}$)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	20	V
Collector-emitter voltage	V _{CEO}	12	V
Emitter-base voltage	V _{EBO}	3	V
Base current	I _B	40	mA
Collector current	I _C	80	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _j	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Microwave Characteristics (Ta = 25°C)

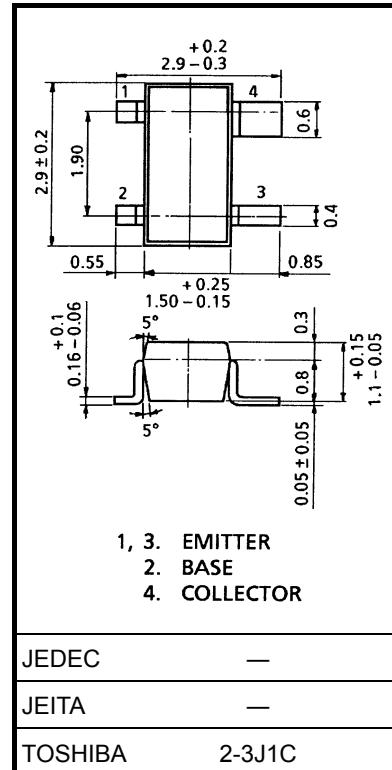
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Transition frequency	f _T	V _{CE} = 10 V, I _C = 20 mA	5	7	—	GHz
Insertion gain	S _{21e} ² (1)	V _{CE} = 10 V, I _C = 20 mA, f = 500 MHz	—	18	—	dB
	S _{21e} ² (2)	V _{CE} = 10 V, I _C = 20 mA, f = 1 GHz	9.5	13	—	
Noise figure	NF (1)	V _{CE} = 10 V, I _C = 5 mA, f = 500 MHz	—	1	—	dB
	NF (2)	V _{CE} = 10 V, I _C = 5 mA, f = 1 GHz	—	1.1	2	

Electrical Characteristics (Ta = 25°C)

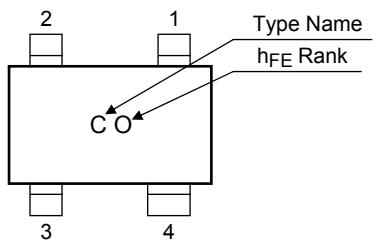
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I _{CB0}	V _{CB} = 10 V, I _E = 0	—	—	1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 1 V, I _C = 0	—	—	1	μA
DC current gain	h _{FE} (Note 1)	V _{CE} = 10 V, I _C = 20 mA	80	—	240	
Output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz (Note 2)	—	1.1	1.6	pF
Reverse transfer capacitance	C _{re}		—	0.65	1.05	pF

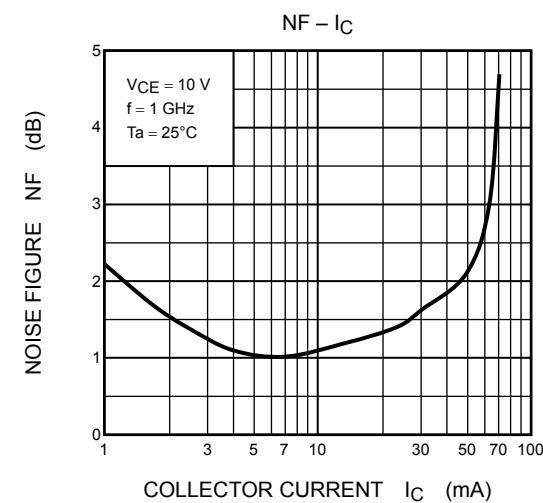
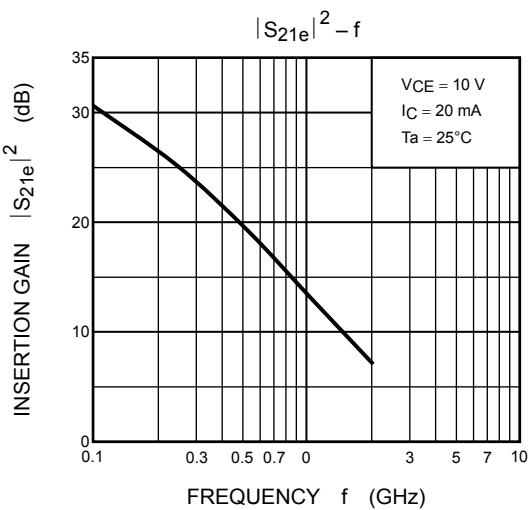
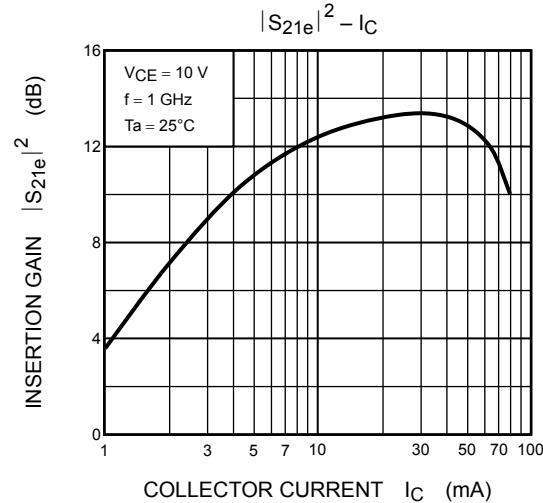
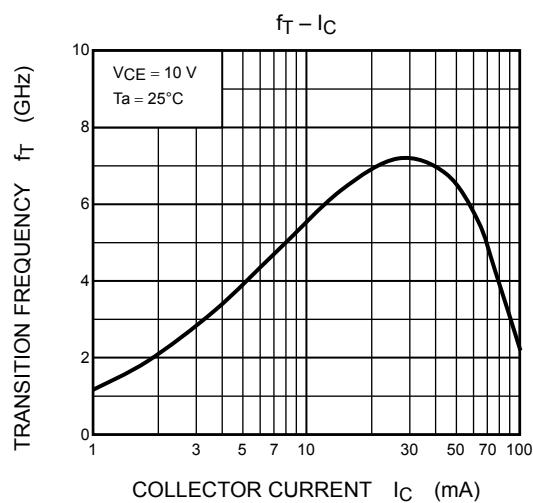
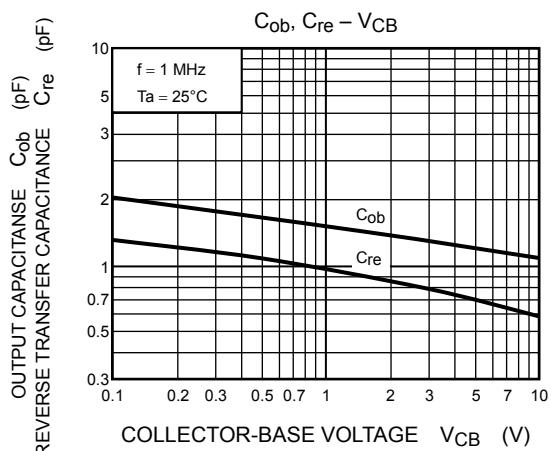
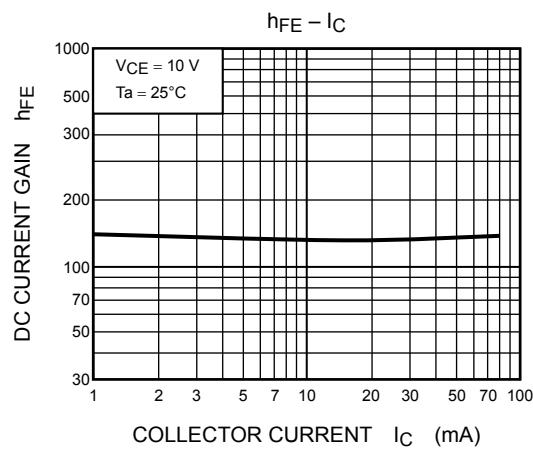
Note 1: h_{FE} classification O: 80~160, Y: 120~240

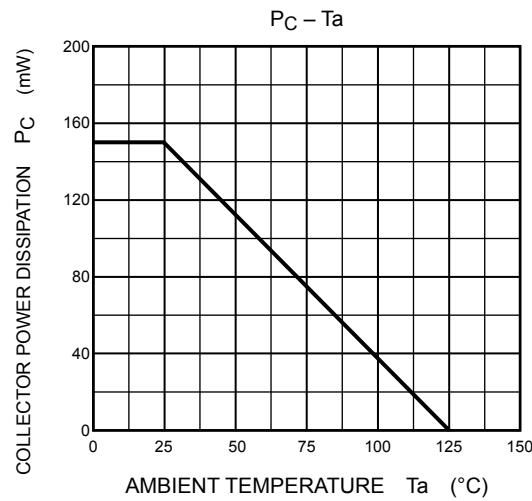
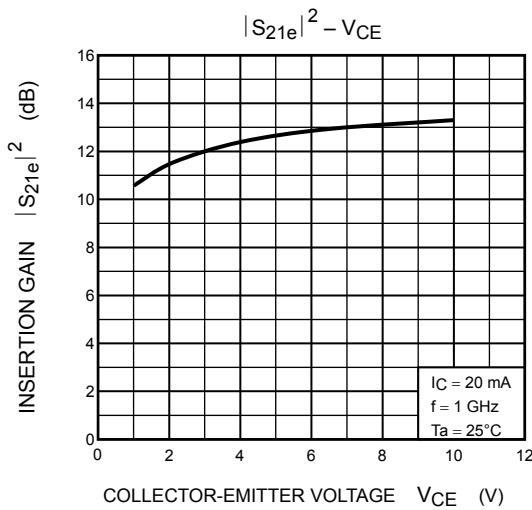
Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.



Weight: 0.012 g (typ.)

Marking





S-Parameter $Z_0 = 50 \Omega$, $T_a = 25^\circ\text{C}$

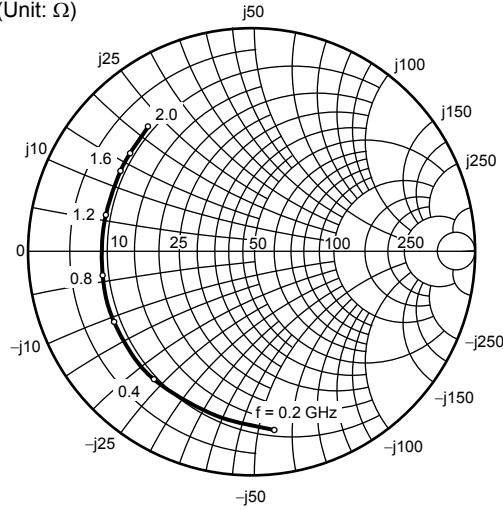
$V_{CE} = 10 \text{ V}$, $I_C = 5 \text{ mA}$

Frequency	S11		S21		S12		S22	
	MHz	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.
200	0.793	-82.4	11.923	133.4	0.050	52.7	0.788	-36.4
400	0.736	-128.0	7.835	108.5	0.066	38.0	0.584	-53.4
600	0.719	-152.1	5.578	94.5	0.071	34.1	0.490	-63.5
800	0.701	-168.6	4.279	84.4	0.073	33.9	0.445	-72.2
1000	0.698	178.9	3.451	76.6	0.074	36.7	0.424	-80.5
1200	0.697	168.3	2.855	69.9	0.076	40.8	0.413	-88.9
1400	0.699	159.4	2.440	64.0	0.078	46.6	0.404	-97.3
1600	0.703	150.8	2.121	59.3	0.084	52.5	0.401	-105.4
1800	0.713	142.9	1.876	54.5	0.091	58.3	0.398	-112.6
2000	0.722	134.7	1.681	50.3	0.100	63.5	0.398	-119.6

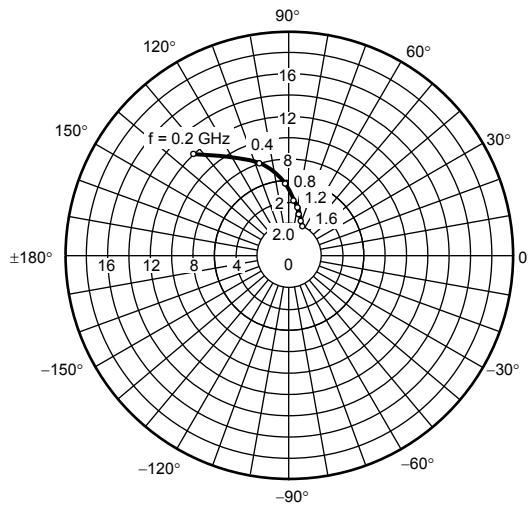
$V_{CE} = 10 \text{ V}$, $I_C = 20 \text{ mA}$

Frequency	S11		S21		S12		S22	
	MHz	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.
200	0.655	-129.4	20.724	113.2	0.031	48.0	0.496	-59.6
400	0.650	-161.5	11.288	95.5	0.040	50.4	0.319	-74.1
600	0.660	-176.3	7.643	86.4	0.049	56.4	0.263	-83.5
800	0.666	172.8	5.758	79.6	0.059	60.0	0.242	-92.9
1000	0.667	164.0	4.605	74.2	0.070	63.6	0.233	-102.0
1200	0.668	156.8	3.809	69.3	0.080	65.9	0.229	-111.0
1400	0.677	148.4	3.277	65.1	0.091	68.2	0.226	-119.1
1600	0.676	141.1	2.862	61.2	0.104	70.0	0.223	-126.5
1800	0.688	133.9	2.559	57.5	0.117	71.2	0.220	-132.4
2000	0.690	126.7	2.303	54.1	0.131	72.4	0.217	-137.8

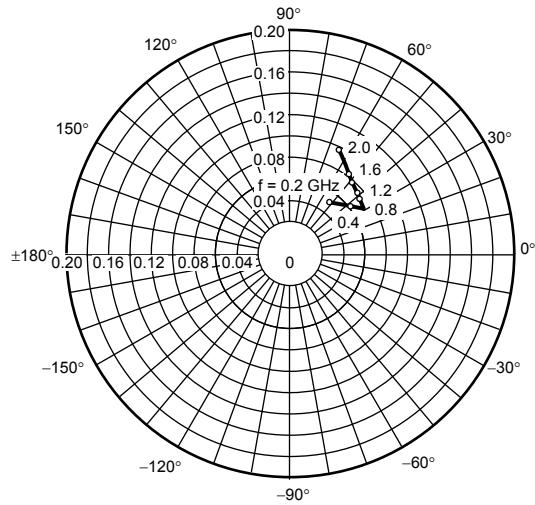
S_{11e}
 $V_{CE} = 10$ V
 $I_C = 5$ mA
 $T_a = 25^\circ\text{C}$
(Unit: Ω)



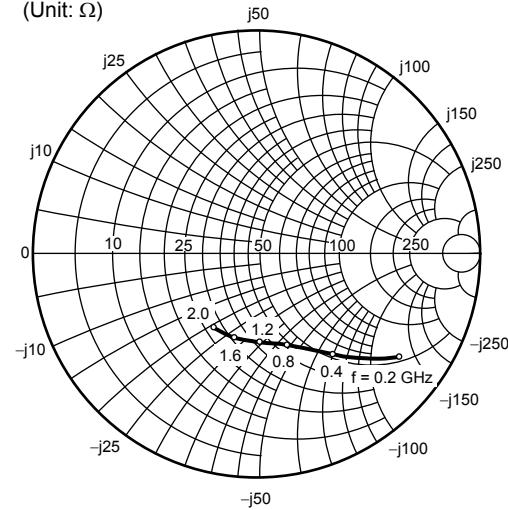
S_{21e}
 $V_{CE} = 10$ V
 $I_C = 5$ mA
 $T_a = 25^\circ\text{C}$



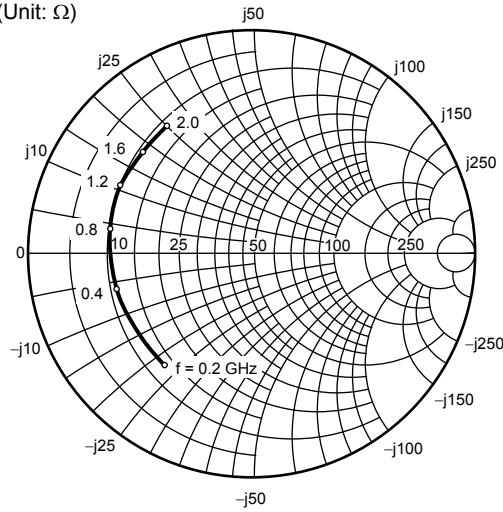
S_{12e}
 $V_{CE} = 10$ V
 $I_C = 5$ mA
 $T_a = 25^\circ\text{C}$



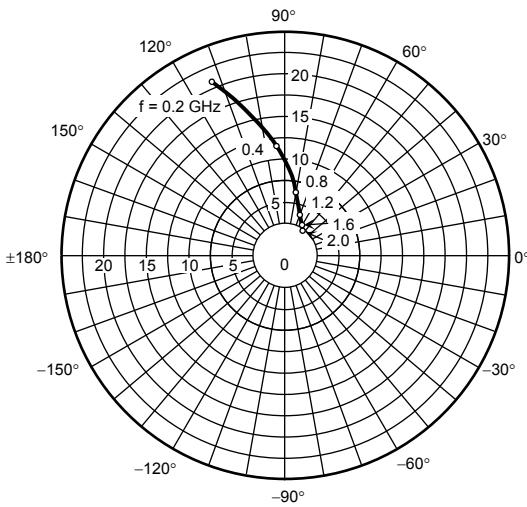
S_{22e}
 $V_{CE} = 10$ V
 $I_C = 5$ mA
 $T_a = 25^\circ\text{C}$
(Unit: Ω)



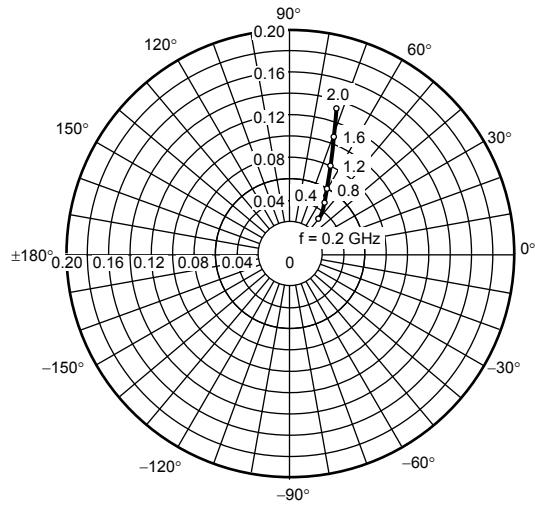
S_{11e}
 $V_{CE} = 10$ V
 $I_C = 20$ mA
 $T_a = 25^\circ\text{C}$
(Unit: Ω)



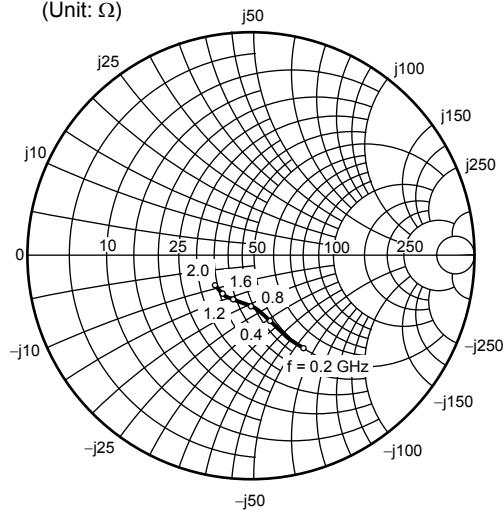
S_{21e}
 $V_{CE} = 10$ V
 $I_C = 20$ mA
 $T_a = 25^\circ\text{C}$



S_{12e}
 $V_{CE} = 10$ V
 $I_C = 20$ mA
 $T_a = 25^\circ\text{C}$



S_{22e}
 $V_{CE} = 10$ V
 $I_C = 20$ mA
 $T_a = 25^\circ\text{C}$
(Unit: Ω)



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20070701-EN GENERAL

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